



#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	I <sub>D MAX</sub> Ta = +25°C
	$29m\Omega @ V_{GS} = 4.5V$	5.6A
12V	$34m\Omega$ @ V <sub>GS</sub> = 2.5V	5.1A
120	44mΩ @ V <sub>GS</sub> = 1.8V	4.5A
	$65m\Omega @ V_{GS} = 1.5V$	3.7A

### **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

#### **Applications**

- Load switches
- Power-management functions
- Portable power adaptors

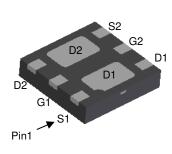
#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

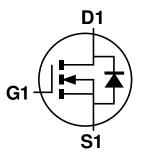
#### **Mechanical Data**

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

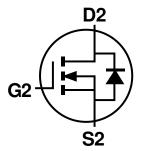
#### U-DFN2020-6 (Type B)



**Bottom View** 



Q1 N-CHANNEL MOSFET



**Q2 N-CHANNEL MOSFET** 

Internal Schematic

## Ordering Information (Note 4)

Part Number	Paakana	Packing		
Part Number	Package	Qty.	Carrier	
DMN1029UFDB-7	U-DFN2020-6 (Type B)	3000	Tape & Reel	
DMN1029UFDB-13	U-DFN2020-6 (Type B)	10000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**

Site 1



D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: K = 2023) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	С		K	L	М	N	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



D5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 3 = 2023)

W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Υ	ear	2015	 2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
C	ode	5	 3	4	5	6	7	8	9	0	1	2

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	Χ	Υ	Z



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	12	V	
Gate-Source Voltage			$V_{GSS}$	±8	V
Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			lo	5.6 4.4	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	t < 5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lο	7.2 5.8	А
Maximum Continuous Body Diode Forward Curre	ent (Note 5)		Is	1	Α
Pulsed Drain Current (10µs pulse, Duty Cycle =		lрм	20	Α	
Avalanche Current (L = 0.1mH)			las	15	Α
Avalanche Energy (L = 0.1mH)			Eas	12	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Bower Dissipation (Note 5)	Steady State	D-	1.4	W
Total Power Dissipation (Note 5)	t < 5s	$P_{D}$	2.2	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	В	91	
memai hesistance, junction to Ambient (Note 5)	t < 5s	$R_{ hetaJA}$	55	°C/W
Thermal Resistance, Junction to Case	Rелс	20		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

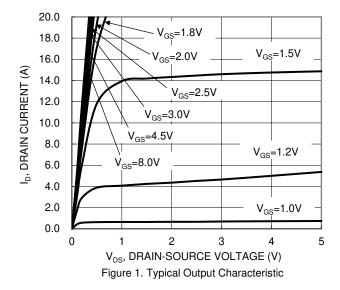
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	12	_	_	V	$V_{GS} = 0V$ , $I_D = 250 \mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	1.0	μΑ	V <sub>DS</sub> = 12V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						•
Gate Threshold Voltage	Vgs(TH)	0.4	_	1	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
		_	17	29		$V_{GS} = 4.5V, I_{D} = 5A$
Chatia Duain Causaa On Danistassa		_	20	34	mΩ	$V_{GS} = 2.5V, I_{D} = 4.6A$
Static Drain-Source On-Resistance	RDS(ON)	_	24	44	mΩ	V <sub>G</sub> S = 1.8V, I <sub>D</sub> = 4.1A
		_	30	65		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 2A
Diode Forward Voltage	V <sub>SD</sub>	_	0.6	1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 1A
DYNAMIC CHARACTERISTICS (Note 7)						•
Input Capacitance	Ciss		914	_	рF	.,
Output Capacitance	Coss	_	132	_	рF	V <sub>DS</sub> = 6V, V <sub>GS</sub> = 0V, -f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	119	_	рF	1 = 1.000112
Gate Resistance	Rg	_	1.26	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 4.5V)		_	10.5	_	nC	
Total Gate Charge (VGS = 8V)	Qg	_	19.6	_	nC	],, o,,, o,,,
Gate-Source Charge	Qgs	_	1.2	_	nC	$V_{DS} = 6V, I_{D} = 6.5A$
Gate-Drain Charge	Q <sub>qd</sub>	_	1.6	_	nC	7
Turn-On Delay Time	tD(ON)	_	5.0	_	ns	
Turn-On Rise Time	tR	_	10.5	_	ns	$V_{DD} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	tD(OFF)		16.6	_	ns	$R_L = 1.2\Omega$ , $R_G = 1\Omega$
Turn-Off Fall Time	tF		4.1		ns	

5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

#### DMN1029UFDB





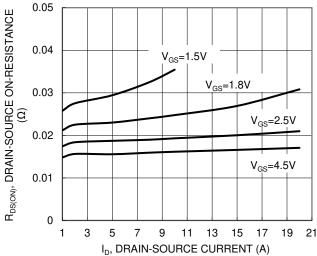


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

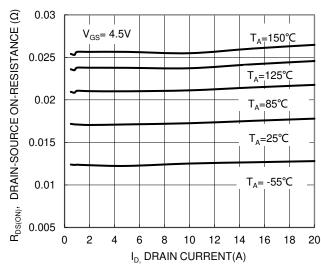
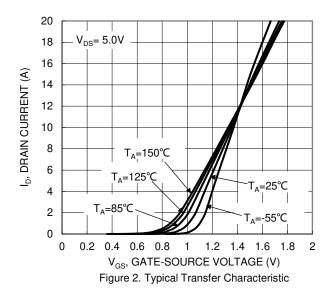
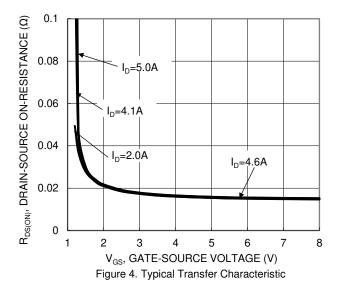


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





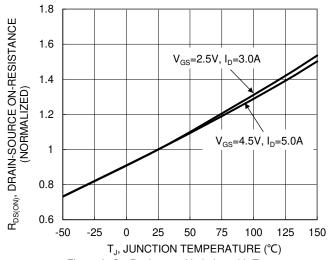


Figure 6. On-Resistance Variation with Temperature

## DMN1029UFDB



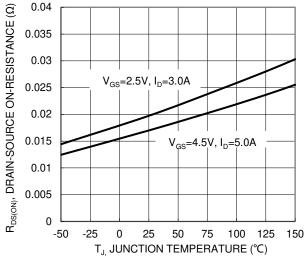


Figure 7. On-Resistance Variation with Temperature

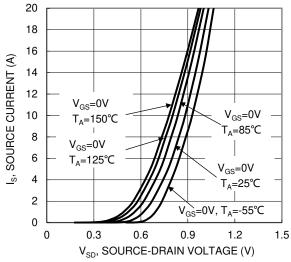
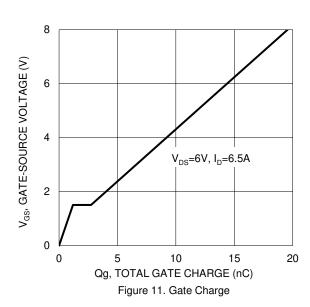


Figure 9. Diode Forward Voltage vs. Current



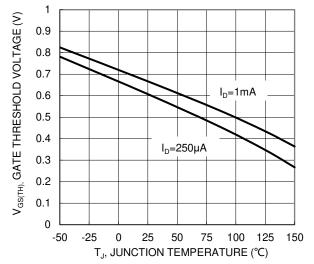
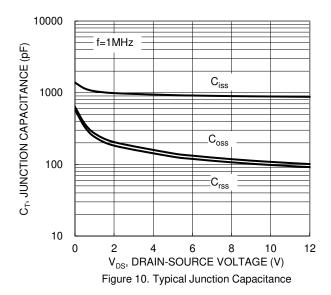


Figure 8. Gate Threshold Variation vs. Junction Temperature



100  $R_{\text{DS}(\text{ON})}$  Limited DRAIN CURRENT (A) 10 T<sub>JMax)</sub>=150°C  $T_A=25$ °C  $P_w=10s$ 0.1 ف\_ Single Pulse DUT on 1\*MRP board -DÇ  $V_{GS}=4.5V$ 0.01 0.01 100 V<sub>DS</sub> DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



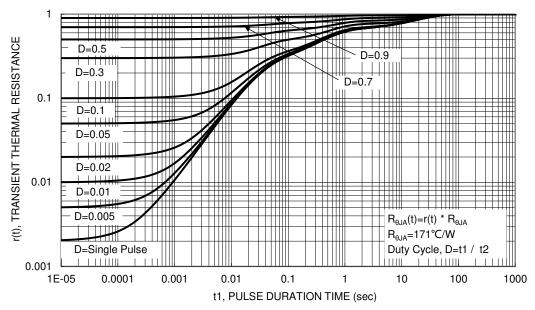


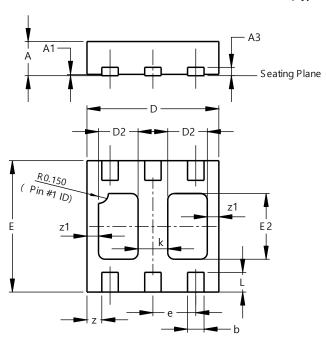
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type B)

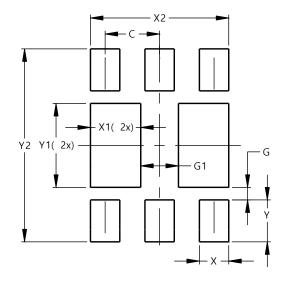


	U-DFN2020-6 Type B							
Dim	Min   Max   Typ							
Α	0.545	0.605	0.575					
A1	0.00	0.05	0.02					
A3	-	-	0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
D2	0.50	0.70	0.60					
е	1	-	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
k	-	-	0.45					
L	0.25	0.35	0.30					
Z	-	-	0.225					
z1	-	-	0.175					
All	Dimens	ions in	mm					

# **Suggested Pad Layout**

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

#### U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Υ	0.500
Y1	1.000
Y2	2.300



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